

Mingxing Wang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

274
papers

5,753
citations

36
h-index

65
g-index

295
ext. papers

6,447
ext. citations

4.4
avg, IF

5.26
L-index

#	Paper	IF	Citations
274	Correlation between electrical properties and growth dynamics for Si-doped Al-rich AlGa _N grown by metal-organic chemical vapor deposition. <i>Superlattices and Microstructures</i> , 2022 , 107141	2.8	2
273	Effect of unintentional nitrogen incorporation on n-type doping of Ga ₂ O ₃ grown by molecular beam epitaxy. <i>CrystEngComm</i> , 2022 , 24, 269-274	3.3	3
272	High electron mobility in nearly-dislocation-free hexagonal InN. <i>Applied Physics Express</i> , 2022 , 15, 011004	4.4	1
271	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2022 , 28, 1-7	3.8	
270	Unidirectional Elimination of Hydrogen by a Giant Local Field Saves First- and Last-Mile Performances of Semiconductor Devices.. <i>Journal of Physical Chemistry Letters</i> , 2022 , 2084-2093	6.4	0
269	Sub-nanometer ultrathin epitaxy of AlGa _N and its application in efficient doping.. <i>Light: Science and Applications</i> , 2022 , 11, 71	16.7	3
268	Deep ultraviolet micro-LEDs exhibiting high output power and high modulation bandwidth simultaneously.. <i>Advanced Materials</i> , 2022 , e2109765	24	8
267	Ultra-thin AlGa _N /Ga _N HFET with a high breakdown voltage on sapphire substrates. <i>Applied Physics Letters</i> , 2021 , 119, 252101	3.4	1
266	Lattice Polarity Manipulation of Quasi-vdW Epitaxial Ga _N Films on Graphene Through Interface Atomic Configuration. <i>Advanced Materials</i> , 2021 , e2106814	24	2
265	Exciton-polariton properties of hexagonal BN-based microcavity and their potential applications in BEC and superconductivity. <i>Physical Review B</i> , 2021 , 104,	3.3	1
264	Transferable room-temperature single-photon emitters in hexagonal boron nitride grown by molecular beam epitaxy. <i>AIP Advances</i> , 2021 , 11, 115101	1.5	1
263	Interfacial symmetry breaking induced spin-orbit coupling in wurtzite Ga _N nanowires. <i>Applied Physics Letters</i> , 2021 , 118, 122104	3.4	1
262	Control of dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies introduced through thermal desorption of heteroatoms. <i>Applied Physics Letters</i> , 2021 , 118, 162103	3.4	2
261	Microstructure and dislocation evolution in composition gradient AlGa _N grown by MOCVD. <i>Superlattices and Microstructures</i> , 2021 , 152, 106842	2.8	1
260	Structure and luminescence of a-plane Ga _N on r-plane sapphire substrate modified by Si implantation*. <i>Chinese Physics B</i> , 2021 , 30, 056104	1.2	
259	High-mobility n-Ga _N drift layer grown on Si substrates. <i>Applied Physics Letters</i> , 2021 , 118, 222106	3.4	1
258	Improved Ohmic contacts to plasma etched high Al fraction n-AlGa _N by active surface pretreatment. <i>Applied Physics Letters</i> , 2021 , 118, 222101	3.4	1

257	Demonstration of epitaxial growth of strain-relaxed GaN films on graphene/SiC substrates for long wavelength light-emitting diodes. <i>Light: Science and Applications</i> , 2021 , 10, 117	16.7	14
256	Color-Tunable 3D InGaN/GaN Multi-Quantum-Well Light-Emitting-Diode Based on Microfacet Emission and Programmable Driving Power Supply. <i>Advanced Optical Materials</i> , 2021 , 9, 2001400	8.1	8
255	Controlling Phase-Coherent Electron Transport in III-Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaIn/GaN Double Barrier Structures. <i>Advanced Functional Materials</i> , 2021 , 31, 2007216	15.6	7
254	Realization of high efficiency AlGaIn-based multiple quantum wells grown on nano-patterned sapphire substrates. <i>CrystEngComm</i> , 2021 , 23, 1201-1206	3.3	5
253	Improved light extraction efficiency of AlGaIn deep-ultraviolet light emitting diodes combining Ag-nanodots/Al reflective electrode with highly transparent p-type layer. <i>Optics Express</i> , 2021 , 29, 2394-2401	3.2	7
252	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGaIn buffer layer. <i>Applied Physics Letters</i> , 2021 , 118, 052104	3.4	7
251	Carrier Velocity Modulation by Asymmetrical Concave Quantum Barriers to Improve the Performance of AlGaIn-Based Deep Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-8	1.8	1
250	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. <i>Advanced Functional Materials</i> , 2021 , 31, 2009771	15.6	4
249	Reduced thermal boundary conductance in GaN-based electronic devices introduced by metal bonding layer. <i>Nano Research</i> , 2021 , 14, 3616-3620	10	1
248	Monolayer-Scale GaN/AlN Multiple Quantum Wells for High Power e-Beam Pumped UV-Emitters in the 240-270 nm Spectral Range. <i>Nanomaterials</i> , 2021 , 11,	5.4	3
247	Multi-channel AlGaIn/GaN Schottky barrier diodes with a half through-hole. <i>Materials Science in Semiconductor Processing</i> , 2021 , 133, 105934	4.3	0
246	Material epitaxy of AlN thin films. <i>Semiconductors and Semimetals</i> , 2021 , 107, 283-311	0.6	
245	Four-inch high quality crack-free AlN layer grown on a high-temperature annealed AlN template by MOCVD. <i>Journal of Semiconductors</i> , 2021 , 42, 122804	2.3	4
244	High quality AlN with uniform in-plane strain on nano-patterned AlN templates achieved by preset strain modulation. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 120903	1.4	1
243	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. <i>Applied Physics Letters</i> , 2020 , 117, 133106	3.4	1
242	Excitation and emission dynamics of a single photon emitting InGaIn quantum dot in a photonic horn structure. <i>Superlattices and Microstructures</i> , 2020 , 145, 106575	2.8	1
241	Controlled bunching approach for achieving high efficiency active region in AlGaIn-based deep ultraviolet light-emitting devices with dual-band emission. <i>Applied Physics Letters</i> , 2020 , 116, 212102	3.4	7
240	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. <i>Applied Physics Letters</i> , 2020 , 116, 232105	3.4	10

239	III-nitrides based resonant tunneling diodes. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 253002	3	2
238	Graphene-Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Non-Polar Sapphire Substrates for Green Light Emitting Diodes. <i>Advanced Functional Materials</i> , 2020 , 30, 2001283	15.6	21
237	3D-Ising critical behavior in antiperovskite-type ferromagneticlike Mn ₃ GaN. <i>Journal of Applied Physics</i> , 2020 , 127, 073903	2.5	
236	A GaN/AlN quantum cascade detector with a broad response from the mid-infrared (4.1 μ m) to the visible (550 nm) spectral range. <i>Applied Physics Letters</i> , 2020 , 116, 171102	3.4	6
235	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. <i>Physical Review Materials</i> , 2020 , 4,	3.2	10
234	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , 2020 , 8, 610	6	5
233	Full-composition-graded In _x Ga _{1-x} N films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020 , 117, 182101	3.4	2
232	Stress evolution in AlN growth on nano-patterned sapphire substrates. <i>Applied Physics Express</i> , 2020 , 13, 015504	2.4	6
231	Hexagonal BN-Assisted Epitaxy of Strain Released GaN Films for True Green Light-Emitting Diodes. <i>Advanced Science</i> , 2020 , 7, 2000917	13.6	11
230	Three Subband Occupation of the Two-Dimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. <i>Advanced Functional Materials</i> , 2020 , 30, 2004450	15.6	4
229	Influence of high-energy local orbitals and electron-phonon interactions on the band gaps and optical absorption spectra of hexagonal boron nitride. <i>Physical Review B</i> , 2020 , 102,	3.3	7
228	Direct evidence of hydrogen interaction with carbon: CH complex in semi-insulating GaN. <i>Applied Physics Letters</i> , 2020 , 116, 262101	3.4	8
227	Nanopatterned sapphire substrate to enhance the efficiency of AlGaIn-based UVC light source tube with CNT electron-beam. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 17336-17341	7.1	0
226	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. <i>Applied Physics Letters</i> , 2020 , 117, 022103	3.4	7
225	Investigation of carrier compensation traps in n-GaN drift layer by high-temperature deep-level transient spectroscopy. <i>Applied Physics Letters</i> , 2020 , 117, 112103	3.4	5
224	Single-photon emission from isolated monolayer islands of InGaIn. <i>Light: Science and Applications</i> , 2020 , 9, 159	16.7	11
223	Conductive transparent (InGa) ₂ O ₃ film as host for rare earth Eu. <i>AIP Advances</i> , 2020 , 10, 025024	1.5	
222	Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020 , 116, 142104	3.4	9

221	Sec-Eliminating the SARS-CoV-2 by AlGa _N Based High Power Deep Ultraviolet Light Source. <i>Advanced Functional Materials</i> , 2020 , 31, 2008452	15.6	32
220	Period size effect induced crystalline quality improvement of AlN on a nano-patterned sapphire substrate. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 100912	1.4	5
219	Puzzle of non-surface related 2D electron gas in n-InN epitaxial samples. <i>Journal of Applied Physics</i> , 2019 , 126, 045705	2.5	1
218	Realization of low dislocation density AlN on a small-coalescence-area nano-patterned sapphire substrate. <i>CrystEngComm</i> , 2019 , 21, 2490-2494	3.3	22
217	Dominant Influence of Interface Roughness Scattering on the Performance of GaN Terahertz Quantum Cascade Lasers. <i>Nanoscale Research Letters</i> , 2019 , 14, 206	5	6
216	Single-photon emission from a further confined InGa _N /Ga _N quantum disc via reverse-reaction growth. <i>Quantum Engineering</i> , 2019 , 1, e20	4.5	15
215	High performance of AlGa _N deep-ultraviolet light emitting diodes due to improved vertical carrier transport by delta-accelerating quantum barriers. <i>Applied Physics Letters</i> , 2019 , 114, 172105	3.4	14
214	Influence of intrinsic or extrinsic doping on lattice locations of carbon in semi-insulating Ga _N . <i>Applied Physics Express</i> , 2019 , 12, 061002	2.4	5
213	High-temperature annealing induced evolution of strain in AlN epitaxial films grown on sapphire substrates. <i>Applied Physics Letters</i> , 2019 , 114, 112105	3.4	36
212	Deep Ultraviolet Light Source from Ultrathin Ga _N /Al _N MQW Structures with Output Power Over 2 Watt. <i>Advanced Optical Materials</i> , 2019 , 7, 1801763	8.1	29
211	Repeatable asymmetric resonant tunneling in AlGa _N /Ga _N double barrier structures grown on sapphire. <i>Applied Physics Letters</i> , 2019 , 114, 073503	3.4	10
210	Migration of carbon from Ga sites to N sites in Ga _N : a combined PAS and hybrid DFT study. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 090901	1.4	3
209	Single photon source based on an InGa _N quantum dot in a site-controlled optical horn structure. <i>Applied Physics Letters</i> , 2019 , 115, 022101	3.4	8
208	Intensive luminescence from a thick, indium-rich In _{0.7} Ga _{0.3} N film. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 065503	1.4	0
207	Epitaxy of Single-Crystalline Ga _N Film on CMOS-Compatible Si(100) Substrate Buffered by Graphene. <i>Advanced Functional Materials</i> , 2019 , 29, 1905056	15.6	33
206	Impact of Silicon Substrate with Low Resistivity on Vertical Leakage Current in AlGa _N /Ga _N HEMTs. <i>Applied Sciences (Switzerland)</i> , 2019 , 9, 2373	2.6	1
205	The sapphire substrate pretreatment effects on high-temperature annealed AlN templates in deep ultraviolet light emitting diodes. <i>CrystEngComm</i> , 2019 , 21, 4632-4636	3.3	6
204	Experimental Evidence of Large Bandgap Energy in Atomically Thin Al _N . <i>Advanced Functional Materials</i> , 2019 , 29, 1902608	15.6	15

203	Planar anisotropic Shubnikov-de-Haas oscillations of two-dimensional electron gas in AlN/GaN heterostructure. <i>Applied Physics Letters</i> , 2019 , 115, 152107	3.4	3
202	Greatly enhanced performance of AlGaIn-based deep ultraviolet light emitting diodes by introducing a polarization modulated electron blocking layer. <i>Optics Express</i> , 2019 , 27, A1458-A1466	3.3	9
201	Determination of electron effective mass in InN by cyclotron resonance spectroscopy. <i>Superlattices and Microstructures</i> , 2019 , 136, 106318	2.8	1
200	Recombination processes in Mg doped wurtzite InN films with p- and n-type conductivity. <i>AIP Advances</i> , 2019 , 9, 015114	1.5	1
199	AlGaInO ₃ thin film grown on sapphire substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Semiconductors</i> , 2019 , 40, 012802	2.3	11
198	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800651	6.4	23
197	Determination of the transition point from electron accumulation to depletion at the surface of In _x Ga _{1-x} N films. <i>Applied Physics Express</i> , 2018 , 11, 021001	2.4	2
196	Electrical properties of surface and interface layers of the N- and In-polar undoped and Mg-doped InN layers grown by PA MBE. <i>Applied Physics Letters</i> , 2018 , 112, 022104	3.4	5
195	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGaIn/GaN heterostructures on Si. <i>Applied Physics Letters</i> , 2018 , 112, 032104	3.4	7
194	High-electron-mobility InN epilayers grown on silicon substrate. <i>Applied Physics Letters</i> , 2018 , 112, 162104	3.4	18
193	High-Mobility Two-Dimensional Electron Gas at InGaIn/InN Heterointerface Grown by Molecular Beam Epitaxy. <i>Advanced Science</i> , 2018 , 5, 1800844	13.6	14
192	k-space imaging of anisotropic 2D electron gas in GaN/GaAlN high-electron-mobility transistor heterostructures. <i>Nature Communications</i> , 2018 , 9, 2653	17.4	28
191	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. <i>Applied Physics Letters</i> , 2018 , 112, 231904	3.4	12
190	Transition of dominant lattice sites of Mg in InN:Mg revealed by Raman scattering. <i>Superlattices and Microstructures</i> , 2018 , 120, 533-539	2.8	1
189	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGaIn quantum wells. <i>Physical Review Materials</i> , 2018 , 2,	3.2	26
188	Effect of indium droplets on growth of InGaIn film by molecular beam epitaxy. <i>Superlattices and Microstructures</i> , 2018 , 113, 650-656	2.8	7
187	Investigation of InGaIn Layer Grown Under In-Rich Condition by Reflectance Difference Spectroscopy Microscope. <i>Journal of Nanoscience and Nanotechnology</i> , 2018 , 18, 7468-7472	1.3	2
186	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. <i>Physical Review Letters</i> , 2018 , 121, 145505	7.4	27

185	Crystal quality evolution of AlN films via high-temperature annealing under ambient N ₂ conditions. <i>CrystEngComm</i> , 2018 , 20, 6613-6617	3.3	21
184	Lattice-Symmetry-Driven Epitaxy of Hierarchical GaN Nanotripods. <i>Advanced Functional Materials</i> , 2017 , 27, 1604854	15.6	14
183	Nanoscale visualization of electronic properties of Al _x Ga _{1-x} N/Al _y Ga _{1-y} N multiple quantum-well heterostructure by spreading resistance microscopy. <i>Journal of Applied Physics</i> , 2017 , 121, 014305	2.5	4
182	Performance improvement of AlGa _N -based deep-ultraviolet light-emitting diodes via asymmetric step-like AlGa _N quantum wells. <i>Superlattices and Microstructures</i> , 2017 , 104, 240-246	2.8	8
181	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. <i>Scientific Reports</i> , 2017 , 7, 42747	4.9	25
180	High quality and uniformity GaN grown on 150mm Si substrate using in-situ NH ₃ pulse flow cleaning process. <i>Superlattices and Microstructures</i> , 2017 , 104, 112-117	2.8	3
179	Excitonic localization at macrostep edges in AlGa _N /AlGa _N multiple quantum wells. <i>Superlattices and Microstructures</i> , 2017 , 104, 397-401	2.8	14
178	Exciton emission of quasi-2D InGa _N in Ga _N matrix grown by molecular beam epitaxy. <i>Scientific Reports</i> , 2017 , 7, 46420	4.9	12
177	Performance improvement of AlGa _N -based deep-ultraviolet light-emitting diodes via Si-doping design of quantum barriers. <i>Superlattices and Microstructures</i> , 2017 , 109, 687-692	2.8	4
176	Enhanced transport properties in InAlGa _N /AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. <i>Applied Physics Letters</i> , 2017 , 110, 172101	3.4	7
175	Hot electron assisted vertical leakage/breakdown in AlGa _N /Ga _N heterostructures on Si substrates. <i>Superlattices and Microstructures</i> , 2017 , 107, 240-245	2.8	4
174	High-quality AlN epitaxy on sapphire substrates with sputtered buffer layers. <i>Superlattices and Microstructures</i> , 2017 , 105, 34-38	2.8	9
173	Influence of MBE growth modes and conditions on spontaneous formation of metallic In nanoparticles and electrical properties of InN matrix. <i>Journal of Crystal Growth</i> , 2017 , 478, 216-219	1.6	2
172	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGa _N -based quantum wells. <i>Scientific Reports</i> , 2017 , 7, 2358	4.9	13
171	Anomalous surface potential behavior observed in InN by photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2017 , 110, 222103	3.4	2
170	Direct evidence of recombination between electrons in InGa _N quantum discs and holes in p-type Ga _N . <i>Optics Express</i> , 2017 , 25, 30664-30671	3.3	1
169	Identifying a doping type of semiconductor nanowires by photoassisted kelvin probe force microscopy as exemplified for Ga _N nanowires. <i>Optical Materials Express</i> , 2017 , 7, 904	2.6	17
168	Anisotropic strain relaxation and high quality AlGa _N /Ga _N heterostructures on Si (110) substrates. <i>Applied Physics Letters</i> , 2017 , 110, 192104	3.4	5

167	Physical origin of Davydov splitting and resonant Raman spectroscopy of Davydov components in multilayer MoTe ₂ . <i>Physical Review B</i> , 2016 , 93,	3-3	77
166	High-Output-Power Ultraviolet Light Source from Quasi-2D GaN Quantum Structure. <i>Advanced Materials</i> , 2016 , 28, 7978-7983	24	54
165	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. <i>Scientific Reports</i> , 2016 , 6, 35934	4-9	92
164	Performance improvement of AlGaIn-based deep-ultraviolet light-emitting diodes by inserting single spike barriers. <i>Superlattices and Microstructures</i> , 2016 , 100, 941-946	2.8	21
163	Growth of high quality and uniformity AlGaIn/GaN heterostructures on Si substrates using a single AlGaIn layer with low Al composition. <i>Scientific Reports</i> , 2016 , 6, 23020	4-9	39
162	Origin of Improved Optical Quality of Monolayer Molybdenum Disulfide Grown on Hexagonal Boron Nitride Substrate. <i>Small</i> , 2016 , 12, 198-203	11	19
161	Large-Scale Synthesis and Systematic Photoluminescence Properties of Monolayer MoS ₂ on Fused Silica. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 18570-6	9.5	22
160	High-resistance GaN epilayers with low dislocation density via growth mode modification. <i>Journal of Crystal Growth</i> , 2016 , 450, 160-163	1.6	5
159	Efficient silicon quantum dots light emitting diodes with an inverted device structure. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 673-677	7.1	48
158	Leakage Current Mechanism of InN-Based Metal-Insulator-Semiconductor Structures with Al ₂ O ₃ as Dielectric Layers. <i>Nanoscale Research Letters</i> , 2016 , 11, 21	5	2
157	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. <i>Nano Letters</i> , 2016 , 16, 1328-34	11.5	30
156	Reflectance difference spectroscopy microscope for circular defects on InN films. <i>Optics Express</i> , 2016 , 24, 15059-70	3-3	2
155	Photoconductivity in In _x Ga _{1-x} N epilayers. <i>Optical Materials Express</i> , 2016 , 6, 815	2.6	2
154	Hot electron induced non-saturation current behavior at high electric field in InAlN/GaN heterostructures with ultrathin barrier. <i>Scientific Reports</i> , 2016 , 6, 37415	4-9	5
153	Edge Dislocations Triggered Surface Instability in Tensile Epitaxial Hexagonal Nitride Semiconductor. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 34108-34114	9.5	5
152	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaIn system. <i>Scientific Reports</i> , 2016 , 6, 25124	4-9	20
151	Spatial identification of traps in AlGaIn/GaN heterostructures by the combination of lateral and vertical electrical stress measurements. <i>Applied Physics Letters</i> , 2016 , 108, 042107	3-4	3
150	Positive temperature coefficient of photovoltaic efficiency in solar cells based on InGaIn/GaN MQWs. <i>Applied Physics Letters</i> , 2016 , 109, 062104	3-4	10

149	Effect of stress on the Al composition evolution in AlGa _N grown using metal organic vapor phase epitaxy. <i>Applied Physics Express</i> , 2016 , 9, 051001	2.4	5
148	Electrical properties of GaN-based heterostructures adopting InAlN/AlGa _N bilayer barriers. <i>Journal of Crystal Growth</i> , 2016 , 447, 1-4	1.6	
147	Growth of high quality n-Al _{0.5} Ga _{0.5} N thick films by MOCVD. <i>Materials Letters</i> , 2016 , 176, 298-300	3.3	7
146	Residual stress in AlN films grown on sapphire substrates by molecular beam epitaxy. <i>Superlattices and Microstructures</i> , 2016 , 93, 27-31	2.8	23
145	Origin of the wide band gap from 0.6 to 2.3 eV in photovoltaic material InN: quantum confinement from surface nanostructure. <i>Journal of Materials Chemistry A</i> , 2016 , 4, 17412-17418	13	5
144	Improvement of p-type conductivity in Al-rich AlGa _N substituted by Mg Ga δdoping (AlN) m/(Ga _N) n (m, n) superlattice. <i>Journal of Alloys and Compounds</i> , 2016 , 686, 484-488	5.7	3
143	Intersubband Transition in GaN/InGa _N Multiple Quantum Wells. <i>Scientific Reports</i> , 2015 , 5, 11485	4.9	10
142	High mobility AlGa _N /Ga _N heterostructures grown on Si substrates using a large lattice-mismatch induced stress control technology. <i>Applied Physics Letters</i> , 2015 , 106, 142106	3.4	37
141	Tuning the graphene work function by uniaxial strain. <i>Applied Physics Letters</i> , 2015 , 106, 043106	3.4	19
140	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. <i>Applied Physics Letters</i> , 2015 , 106, 232102	3.4	7
139	Hysteresis phenomena of the two dimensional electron gas density in lattice-matched InAlN/Ga _N heterostructures. <i>Applied Physics Letters</i> , 2015 , 107, 052102	3.4	5
138	Elastic properties of indium nitrides grown on sapphire substrates determined by nano-indentation: In comparison with other nitrides. <i>AIP Advances</i> , 2015 , 5, 077131	1.5	11
137	Mid-infrared Photoconductive Response in AlGa _N /Ga _N Step Quantum Wells. <i>Scientific Reports</i> , 2015 , 5, 14386	4.9	5
136	Free and bound excitonic effects in Al _{0.5} Ga _{0.5} N/Al _{0.35} Ga _{0.65} N MQWs with different Si-doping levels in the well layers. <i>Scientific Reports</i> , 2015 , 5, 13046	4.9	16
135	Study on AlGa _N P-I-N-I-N solar-blind avalanche photodiodes with Al _{0.45} Ga _{0.55} N multiplication layer. <i>Electronic Materials Letters</i> , 2015 , 11, 1053-1058	2.9	9
134	Epitaxial growth of AlN films on sapphire via a multilayer structure adopting a low- and high-temperature alternation technique. <i>CrystEngComm</i> , 2015 , 17, 7496-7499	3.3	46
133	Evidence of type-II band alignment in III-nitride semiconductors: experimental and theoretical investigation for In _{0.17} Al _{0.83} N/Ga _N heterostructures. <i>Scientific Reports</i> , 2014 , 4, 6521	4.9	13
132	Shear strain induced modulation to the transport properties of graphene. <i>Applied Physics Letters</i> , 2014 , 105, 083108	3.4	16

131	GaN-based substrates and optoelectronic materials and devices. <i>Science Bulletin</i> , 2014 , 59, 1201-1218		3
130	Short period polar and nonpolar m InN/n GaN superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 678-681		2
129	Generation and electric control of spin-valley-coupled circular photogalvanic current in WSe ₂ . <i>Nature Nanotechnology</i> , 2014 , 9, 851-7	28.7	216
128	Identification of helicity-dependent photocurrents from topological surface states in Bi ₂ Se ₃ gated by ionic liquid. <i>Scientific Reports</i> , 2014 , 4, 4889	4.9	44
127	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. <i>Scientific Reports</i> , 2014 , 4, 4371	4.9	19
126	Effects of light illumination on electron velocity of AlGa _x N/GaN heterostructures under high electric field. <i>Applied Physics Letters</i> , 2014 , 105, 242104	3.4	4
125	Temperature-related exciton features on the Ga-/N-Faces of a free-standing HVPE GaN. <i>Optical Materials Express</i> , 2014 , 4, 553	2.6	
124	Effect of injection current on the optical polarization of AlGa _x N-based ultraviolet light-emitting diodes. <i>Optics Express</i> , 2014 , 22, 19589-94	3.3	16
123	Effect of Mg doping on the structural and free-charge carrier properties of InN films. <i>Journal of Applied Physics</i> , 2014 , 115, 163504	2.5	15
122	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. <i>Applied Physics Letters</i> , 2014 , 104, 182103	3.4	41
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